REQUEST OR

ENTINUED EX. MINATION (RCE) TRANSMITTAL

Subsection (b) of 35 U.S.C. § 132, effective on May 29, 2000, provides for continued examination of an utility or plant application filed on or after June 8, 1995.

See The American Inventors Protection Act of 1999 (AIPA).

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Application Number	09/941,476
Filing Date	August 29, 2001/
First Named Inventor	John Whitman
Group Art Unit	1734
Examiner Name	Kevin P. Shortsle
Attorney Docket Number	303.254US4

This is a Request for Continued Examination (RCE) under 37 C.F.R. § 1.114 of the above-identified application entitled <u>SOLVENT PREWET AND METHOD TO DISPENSE THE SOLVENT PREWET</u>.

Submis	sion required under 37 C.F.R. § 1.114		
1	Consider the amendment(s)/reply under 37 C.F.R. § 1.116 previously filed on		
2	Consider the arguments in the Appeal Brief or Reply Brief previously filed on		
3. <u>X</u>	An Amendment Under 37 CFR § 1.116 (16 pages) is enclosed.	RECEIVED	
4	A new power of attorney (_ pages) is enclosed.	SEP 3 0 2002	
5. <u>X</u>	An Information Disclosure Statement is enclosed (1 page) a. 1 Form(s) 1449 b. 7 Copies of IDS Citations	3 1 700	
6. <u>X</u>	A check in the amount of \$740.00 is attached to pay the RCE filing fee required under C.F.R. § 1.17(e).		
7. <u>X</u>	X The Commissioner is hereby authorized to credit overpayments or charge any fees set forth in 37 C.F.R. §§ 1.16 through 1.18 to Deposit Account No. 19-0743.		
8	A petition for extension of time in the prior application (_ pages) is enclosed along with a check in the amount of \$\sum_{\text{to pay}}\$ to pay the extension fee.		
9. <u>X</u>	. X Other: A Clean Version of Specification Paragraphs (1 pg.) and a Clean Version of Pending Claims (14 pages)		
P.O. B	VEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. ox 2938, Minneapolis, MN 55402 (612-373-6900) Atty: Marvi Reg. No. 38 mer Number 21186	n L. Beekman	
CERTIFIC with suffi September	CATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposite cient postage as first class mail, in an envelope addressed to: Commissioner for Patents, Box RCE, Wasler, 2002. Tinc Kohout Signature	d with the United States Postal Service hington, D.C. 20231, on this 16 day of	

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EXPEDITED PROCEDURE - EXAMINING GROUP 1734

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

John Whitman

Examiner: Kevin P. Shortsle

Serial No.:

09/941,476

Group Art Unit: 1734

Filed:

August 29, 2001

Docket: 303.254US4

Title:

SOLVENT PREWET AND METHOD TO DISPENSE THE SOLVENT

PREWET

AMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116 RECEIVED

Box AF

Commissioner for Patents Washington, D.C. 20231

SFD 3.0 2002

1700

In response to the Final Office Action mailed July 16, 2002, please amend the application as follows:

IN THE SPECIFICATION

Please make the paragraph substitution indicated in the appendix entitled Clean Version of Amended Specification Paragraph. The specific changes incorporated in the substitute paragraph are shown in the following marked-up version of the original paragraph:

The paragraph beginning on page 7, line 15 is amended as follows:

Conventional processes primarily employ a three-component photoresist, with either ethyl lactate (EL) or propyleneglycol monomethylether acetate (PGMEA) as the preferred solvent component. Both of these substances have a rather high evaporation rate, however, which shrinks the process control window. To compensate, conventional systems use more photoresist as well as a greater percentage of solvent to total photoresist volume. In contrast, according to one aspect of the present invention, a low vapor-pressure solvent is used. In one embodiment a mixture of aliphatic [esther] ester and diacetone alcohol is used as the solvent component. The ratio of the materials can range from 10% [esther] ester and 90% alcohol, to 30% esther] ester to 70% alcohol. The dissipation rate of this solvent is significantly reduced over consensional solvents because diacetone alcohol has a heavier molecule, creating a very low pressure solvent. The rate of evaporation is up to ten times lower than that of the conventional solvents. One direct result is that semiconductor processing incorporating this type of solvent requires very